



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#35
Amdt H
D. Small's-Logan
1-28-03

In re the Application of:

)

NISHIMOTO et al

) Art Unit: 2823

Serial No.: 08/897,839

) Examiner: K. Eaton

Filed: July 21, 1997

)

For: STRESS-ADJUSTED INSULATING
FILM FORMING METHOD,
SEMICONDUCTOR DEVICE AND
METHOD OF MANUFACTURING THE
SAME

)

RESPONSE TO OFFICE ACTION OF JANUARY 10, 2003

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Responsive to the office action of January 10, 2003, please amend the captioned application as follows:

IN THE CLAIMS:

Please rewrite claim 43 as follows:

43. (Amended Three Times) A stress-adjusted insulating film forming method for forming a multilayered insulating film on a substrate, said method comprising:

(a) forming a first insulating layer with compressive stress;

RECEIVED

JAN 21 2003

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